AMT1222 0.02 – 6GHz Low Noise Amplifier Chip

Key Features:

Frequency range: 0.02 – 6GHz

• Typical gain: 21dB

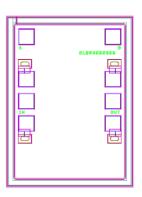
Input standing wave : 1.4Output standing wave : 1.8

• Noise figure: 1.8dB

P-1: 20.2dBm @ +5V/86mA

• Chip dimensions: 0.8mm x 1.1mm x 0.1mm

Applications: wireless communication, transceiver module, radio telecommunication etc.



Description:

AMT1222 chip is a Gallium Arsenide (GaAs) high performance Low Noise Amplifier, it covers 0.02 – 6GHz frequency range. It uses +5V single voltage operation, noise figure is 1.5dB, and 22dB typical gain. This chip is designed with ground through metal vias on the back technology.

Absolute Maximum Ratings (Ta = 25°C)

Symbol	Parameter	Value	Remark			
Vd	Drain Voltage	+7V				
Pin	Input Signal Power	17dBm				
Tch	Operating Temperature	150°C				
Tm	Sintering Temperature	310°C	30s, N₂ protection			
Tstg	Storage Temperature	-65 ~ +150°C				

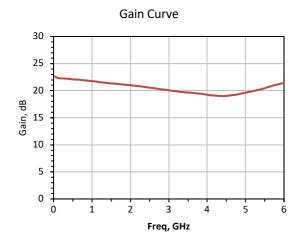
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

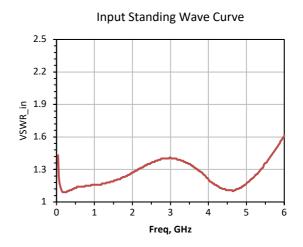
Electrical Characteristics (Ta = 25°C)

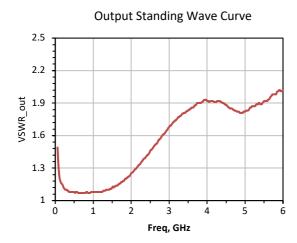
Symbol	mbol Parameter Test Conditions Value			Unit		
Symbol	raiametei	rest conditions	Min	Typical	Max	Onic
G	Gain			21	IVIGA	dB
U			-	21	-	иь
NF	Noise Figure		-	1.8	ı	dB
Id	Static Current	Vd = +5V	-	86	ı	mA
VSWR_in	Input Standing Wave	F : 0.02 ~ 6GHz	-	1.4	1.6	-
VSWR_out	Output Standing Wave		-	1.8	2	-
P-1	Output Power at 1dB point		20.2	20.5	-	dBm

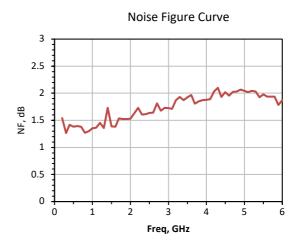
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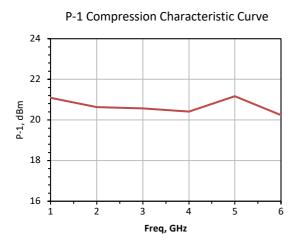
Typical Performance





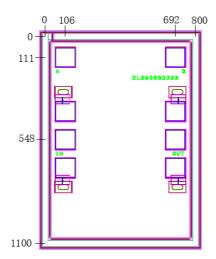




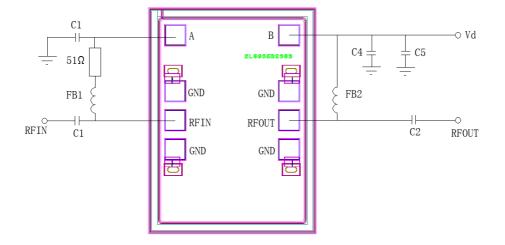


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Chip Dimensions (Unit : μm)



Chip Layout Diagram



Device List

Device Name	Device Model	Value	Manufacturer	Package Type
C1, C2, C3	GRM188R61H102KA01	1000pF	Murata	0603
C4	GRM1885C1H101JA01	100pF	Murata	0603
C5	GRM1857U1A103JA44	10nF	Murata	0603
FB1, FB2	MMZ1005A222ET000	-	TDK	-

Please see Appendix A for details.